PDTC144E series

NPN resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

Rev. 9 — 15 November 2011

Product data sheet

1. Product profile

1.1 General description

NPN Resistor-Equipped Transistor (RET) family in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package		PNP		Package
	NXP	JEITA	JEDEC	complement	configuration
PDTC144EE	SOT416	SC-75	-	PDTA144EE	ultra small
PDTC144EM	SOT883	SC-101	-	PDTA144EM	leadless ultra small
PDTC144ET	SOT23	-	TO-236AB	PDTA144ET	small
PDTC144EU	SOT323	SC-70	-	PDTA144EU	very small

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

1.3 Applications

- Digital applications in automotive and industrial segments
- Control of IC inputs

- Cost-saving alternative for BC847/857 series in digital applications
- Switching loads

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
Io	output current		-	-	100	mA
R1	bias resistor 1 (input)		33	47	61	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	



2. Pinning information

Table 3. **Pinning** Simplified outline **Graphic symbol** Pin Description SOT23; SOT323; SOT416 1 input (base) 3 GND (emitter) 2 3 output (collector) 006aaa144 sym007 **SOT883** 1 input (base) 2 GND (emitter) output (collector) Transparent

3. Ordering information

Table 4. Ordering information

Type number	Package					
	Name	Description	Version			
PDTC144EE	SC-75	plastic surface-mounted package; 3 leads	SOT416			
PDTC144EM	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 \times 0.6 \times 0.5 mm	SOT883			
PDTC144ET	-	plastic surface-mounted package; 3 leads	SOT23			
PDTC144EU	SC-70	plastic surface-mounted package; 3 leads	SOT323			

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PDTC144EE	08
PDTC144EM	E7
PDTC144ET	*08
PDTC144EU	*08

[1] * = placeholder for manufacturing site code

5. Limiting values

Table 6. Limiting values

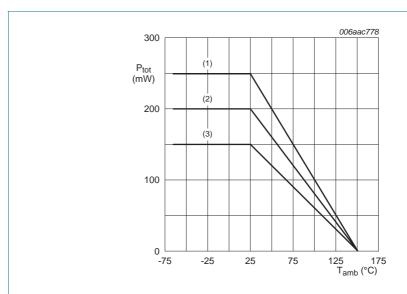
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	50	V
V_{CEO}	collector-emitter voltage	open base	-	50	V
V_{EBO}	emitter-base voltage	open collector	-	10	V
VI	input voltage				
	positive		-	+40	V
	negative		-	-10	V
I _O	output current		-	100	mA
I _{CM}	peak collector current	$single \ pulse; \\ t_p \leq 1 \ ms$	-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	PDTC144EE (SOT416)		[1][2]	150	mW
	PDTC144EM (SOT883)		[2][3]	250	mW
	PDTC144ET (SOT23)		[1] -	250	mW
	PDTC144EU (SOT323)		[1] -	200	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.

^[3] Device mounted on an FR4 PCB with 70 μm copper strip line, standard footprint.



- (1) SOT23; FR4 PCB, standard footprint SOT883; FR4 PCB with 70 μm copper strip line, standard footprint
- (2) SOT323; FR4 PCB, standard footprint
- (3) SOT416; FR4 PCB, standard footprint

Fig 1. Power derating curves

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	PDTC144EE (SOT416)		[1][2]	-	830	K/W
	PDTC144EM (SOT883)		[2][3]	-	500	K/W
	PDTC144ET (SOT23)		[1] -	-	500	K/W
	PDTC144EU (SOT323)		<u>[1]</u> _	-	625	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Reflow soldering is the only recommended soldering method.
- [3] Device mounted on an FR4 PCB with 70 μm copper strip line, standard footprint.

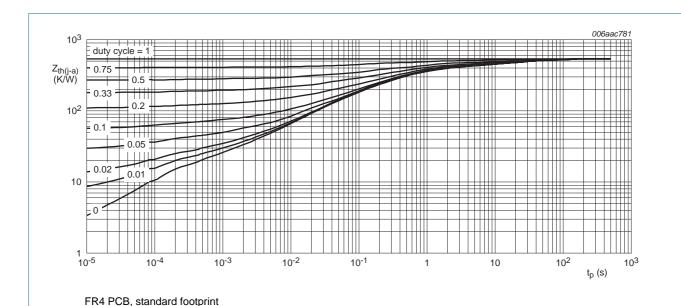
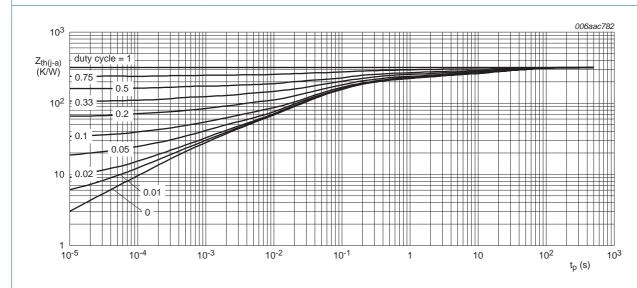


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC144EE (SOT416); typical values



FR4 PCB, 70 µm copper strip line

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC144EM (SOT883); typical values

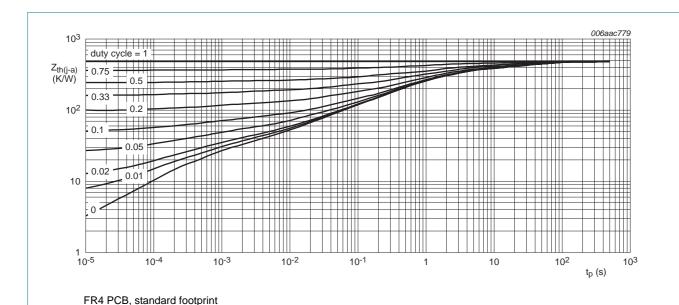


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC144ET (SOT23); typical values

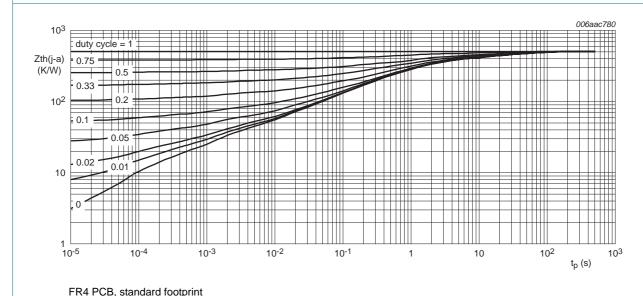


Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC144EU (SOT323); typical values

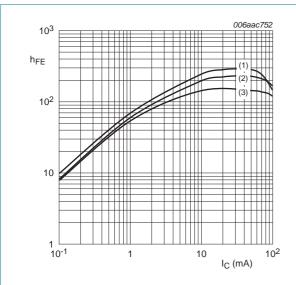
7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I _{CEO}	collector-emitter	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	1	μΑ
CL	cut-off current	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_C = 0 \text{ A}$	-	-	90	μΑ
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}$	80	-	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	-	150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}$	-	1.2	0.8	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 2 \text{ mA}$	3	1.6	-	V
R1	bias resistor 1 (input)		33	47	61	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	2.5	pF
f _T	transition frequency	$V_{CE} = 5 \text{ V; } I_{C} = 10 \text{ mA;}$ f = 100 MHz	<u>[1]</u> -	230	-	MHz

^[1] Characteristics of built-in transistor



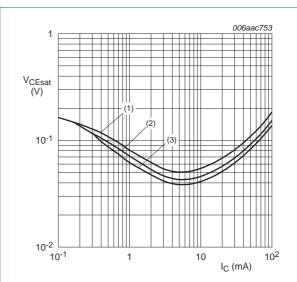
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig 6. DC current gain as a function of collector current; typical values



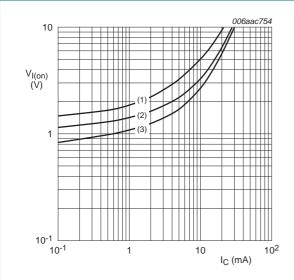
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



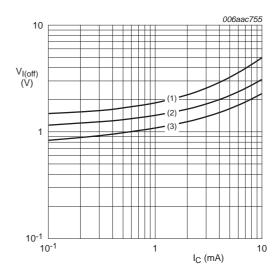
$$V_{CE} = 0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 8. On-state input voltage as a function of collector current; typical values



$$V_{CE} = 5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 9. Off-state input voltage as a function of collector current; typical values

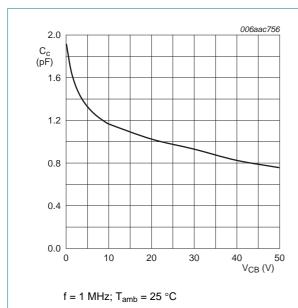


Fig 10. Collector capacitance as a function of collector-base voltage; typical values

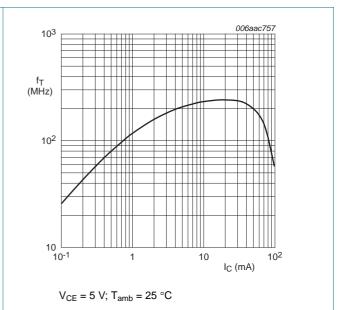


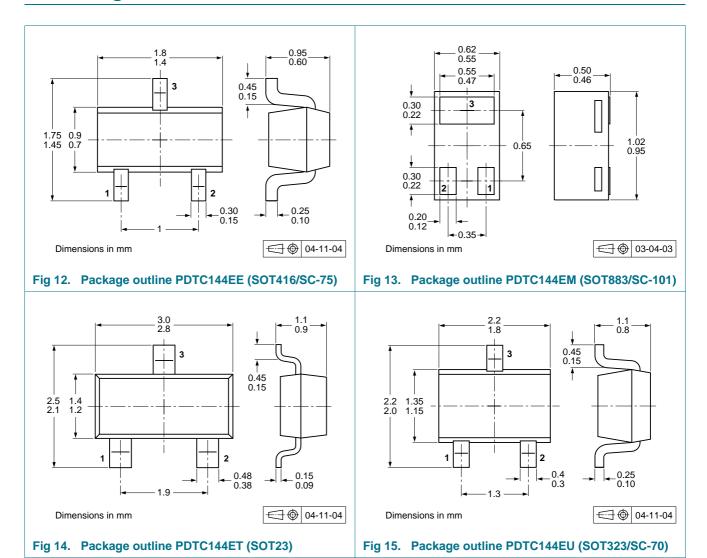
Fig 11. Transition frequency as a function of collector current; typical values of built-in transistor

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity		
			3000	5000	10000
PDTC144EE	SOT416	4 mm pitch, 8 mm tape and reel	-115	-	-135
PDTC144EM	SOT883	2 mm pitch, 8 mm tape and reel	-	-	-315
PDTC144ET	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235
PDTC144EU	SOT323	4 mm pitch, 8 mm tape and reel	-115	-	-135

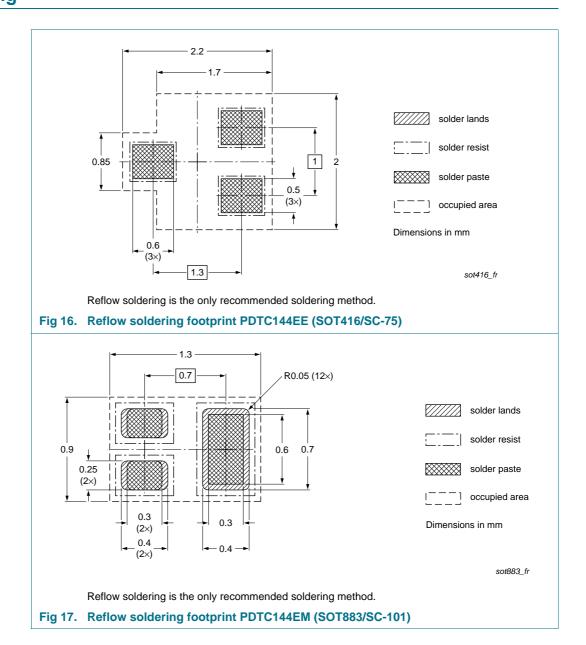
[1] For further information and the availability of packing methods, see Section 14.

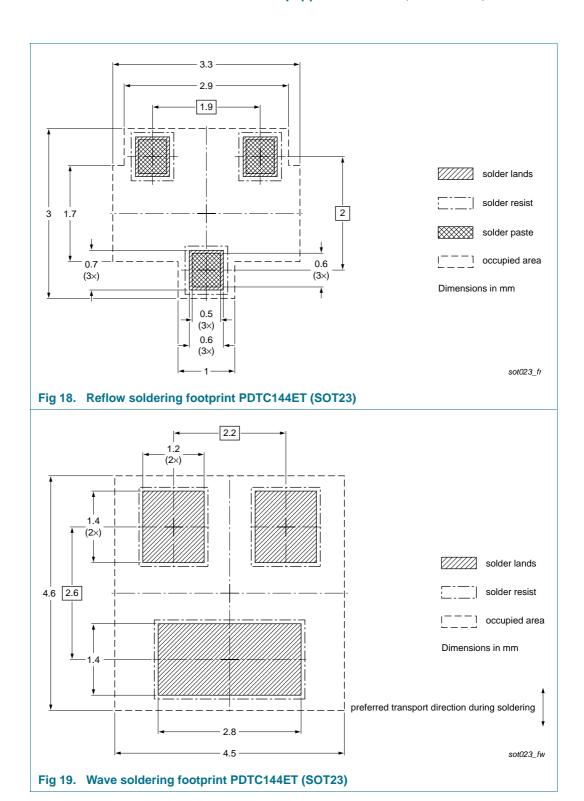
PDTC144E_SER

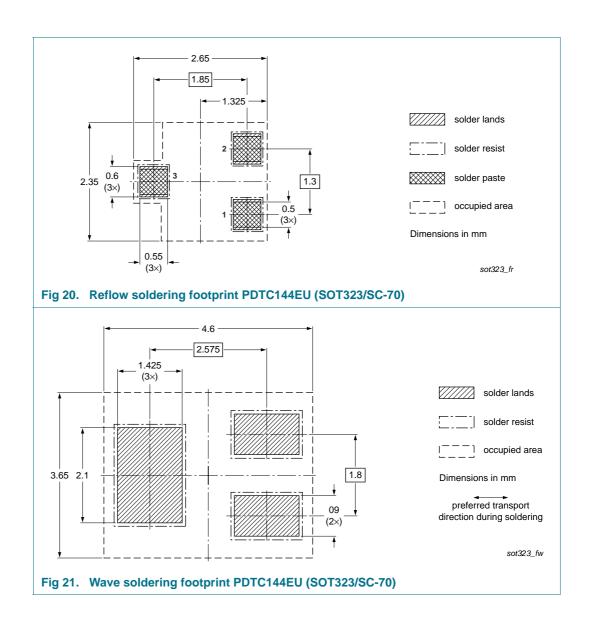
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11. Soldering







12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
PDTC144E_SER v.9	20111115	Product data sheet	-	PDTC144E_SERIES v.8	
Modifications:		f this document has been red NXP Semiconductors.	designed to comply w	th the new identity	
	 Legal texts have 	ave been adapted to the new	company name whe	re appropriate.	
	 Type number 	s PDTC144EEF, PDTC144E	K and PDTC144ES r	emoved.	
	 Section 1 "Pr 	oduct profile": updated			
	 Section 3 "Or 	rdering information": updated			
	 Section 4 "Magnetic Section 4" 	arking": updated			
	• Figure 1 to 1	1: added			
	 Section 6 "Thermal characteristics": updated 				
	• Table 8 "Cha	racteristics": V _{i(on)} redefined	to V _{I(on)} on-state input	voltage, $V_{i(off)}$ redefined	
	to V _{I(off)} off-st	ate input voltage, I _{CEO} updat	ed, f⊤ added		
	 Section 8 "Te 	est information": added			
	 Section 9 "Pa 	ackage outline": superseded	by minimized package	e outline drawings	
	 Section 10 "F 	Packing information": added			
	Section 11 "S	Soldering": added			
	 Section 13 "L 	<u>legal information"</u> : updated			
PDTC144E_SERIES v.8	20040817	Product data sheet	-	PDTC144E_SERIES v.7	
PDTC144E_SERIES v.7	20040323	Product specification	-	PDTC144E_SERIES v.6	
PDTC144E_SERIES v.6	20030414	Product specification	-	-	

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
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PDTC144E series

NPN resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

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PDTC144E series

NPN resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

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